

**IF4500****N-Channel Silicon Junction Field-Effect Transistor**

- Low-Noise, High Gain Amplifier**

**Absolute maximum ratings at  $T_A = 25^\circ\text{C}$** 

Reverse Gate Source & Reverse Gate Drain Voltage	- 20 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	225 mW
Power Derating	1.8 mW/ $^\circ\text{C}$
Storage Temperature Range	- 65 $^\circ\text{C}$ to 200 $^\circ\text{C}$

At 25 $^\circ\text{C}$  free air temperature:**Static Electrical Characteristics**

	IF4500		Process NJ450L		
	Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(\text{BR})\text{GSS}}$	- 20	V	$I_G = - 1 \mu\text{A}$ , $V_{\text{DS}} = \emptyset\text{V}$	
Gate Reverse Current	$I_{\text{GSS}}$		nA	$V_{\text{GS}} = - 30\text{V}$ , $V_{\text{DS}} = \emptyset\text{V}$	
Gate Source Cutoff Voltage	$V_{\text{GS}(\text{OFF})}$	- 0.35	- 1.5	V	$V_{\text{DS}} = 15\text{V}$ , $I_D = 0.5 \text{ nA}$
Drain Saturation Current (Pulsed)	$I_{\text{DSS}}$	5	mA	$V_{\text{DS}} = 15\text{V}$ , $V_{\text{GS}} = \emptyset\text{V}$	

**Dynamic Electrical Characteristics**

Common Source Forward Transconductance	$g_{\text{fs}}$	15		mS	$V_{\text{DS}} = 15\text{V}$ , $I_D = 5 \text{ mA}$	$f = 1 \text{ kHz}$
Common Source Input Capacitance	$C_{\text{iss}}$		35	pF	$V_{\text{DS}} = 15\text{V}$ , $V_{\text{GS}} = \emptyset\text{V}$	$f = 1 \text{ MHz}$
Common Source Reverse Transfer Capacitance	$C_{\text{rss}}$		8	pF	$V_{\text{DS}} = 15\text{V}$ , $V_{\text{GS}} = \emptyset\text{V}$	$f = 1 \text{ MHz}$

Typ

Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$	1.5		nV/ $\sqrt{\text{Hz}}$	$V_{\text{DS}} = 12\text{V}$ , $V_{\text{GS}} = \emptyset\text{V}$	$f = 1 \text{ kHz}$
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**TO-236AB Package**  
Dimensions in Inches (mm)

**Pin Configuration**  
1 Drain, 2 Source, 3 Gate